

Please type a plus sign (+) inside this

#8

PTO/SB/08A (10-96)

Approved for use through 10/31/99. OMB 0651-0031

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

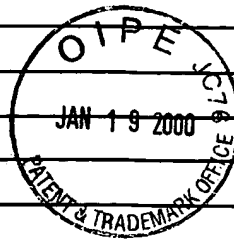
Substitute for form 1449A/PTO  
(Modified by BSTZ 6/30/99)

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Applicant Number	09/096,858
Filing Date	June 12, 1998
First Named Inventor	Narwankar et al.
Group Art Unit	2814
Examiner Name	Mai, A.
Attorney Docket Number	2571.US/RTP/LE



Sheet 1 of 1

**U.S. PATENT DOCUMENTS**

Examiner Initials *	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Filing Date if Appropriate
	Number				
A.M.	5376628		Sekiguchi et al	12/27/1994	3/9/1992
	5290609		Horiike et al	3/1/1994	3/9/1992
	5907780		Gilmer et al.	5/25/1999	6/17/1998

**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Translation? Yes/No
	Office or Country	Number	Date			
A.M.	Japan	03212938 ✓	1/18/1990	Seiko Epson Corp	9/18/1991	Yes
	Japan	04362017 ✓	6/6/1991	Nikko Kyodo Co. Ltd.	12/15/1992	Yes
	Japan	04092423 ✓	8/8/1990	Hitachi Tokyo Electron Co. Ltd.	3/25/1992	Yes
	KR	9500861	2/2/1995	Hundai		Yes
	WO	95/26355 ✓	3/23/1995	Leedham et al	10/5/1995	Yes

**OTHER DOCUMENTS**

Examiner Initials *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published (if known).	Translation? Yes/No
A.M.	MFG. INSULATION LAYER OF CAPACITOR HAVING HIGH DIELECTRIC CONSTANT...Derwent Publications Ltd., London, GB XP002120114 ✓	Yes
	"Low-temperature preparation of SiO <sub>2</sub> /Si(100) interfaces using a two-step remote plasma-assisted oxidation-deposition process", Yasuda, Habermehi, and Lucovsky January 27, 1992 American Institute of Physics pages 434-436 ✓	Yes
	"Nitrogen plasma annealing for low temperature Ta <sub>2</sub> O <sub>5</sub> Films" Aiers, Fleming, Wong, Dennis and Pinczuk. 1998 American Institute of Physics Lucent Technologies NJ pgs. 1308-1310 ✓	Yes
	Enclosed copy of International Search Report	Yes

Examiner  
Signature

ANH D. MAI

Date  
Considered

4/14/00

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.